

Abstracts

A 155-GHz monolithic InP-based HEMT amplifier

H. Wang, R. Lai, Y.C. Chen, Y.L. Kok, T.W. Huang, T. Block, D. Streit, P.H. Liu, P. Siegel and B. Allen. "A 155-GHz monolithic InP-based HEMT amplifier." 1997 MTT-S International Microwave Symposium Digest 3. (1997 Vol. III [MWSYM]): 1275-1278.

This paper presents the development, of a three-stage 155-GHz monolithic low noise amplifier (LNA) using 0.1- μm pseudomorphic (PM) InAlAs/InGaAs/InP HEMT technology. This amplifier exhibits a measured small signal gain of 12 dB at 153-155 GHz, and more than 10-dB gain from 151 to 156 GHz. This is the highest frequency amplifier ever reported using three terminal devices.

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